

# 3D-MAPS: 3D Massively Parallel Processor With Stacked Memory

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# Agenda

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- Objective and Overview
- TSV and Stacking Technology
- Design
  - Architecture, layouts, and design analysis
- Testing
  - Die photos, package, board, and testing Infrastructure
- Measurement Results
- Ongoing Works
- Conclusions

# Objective

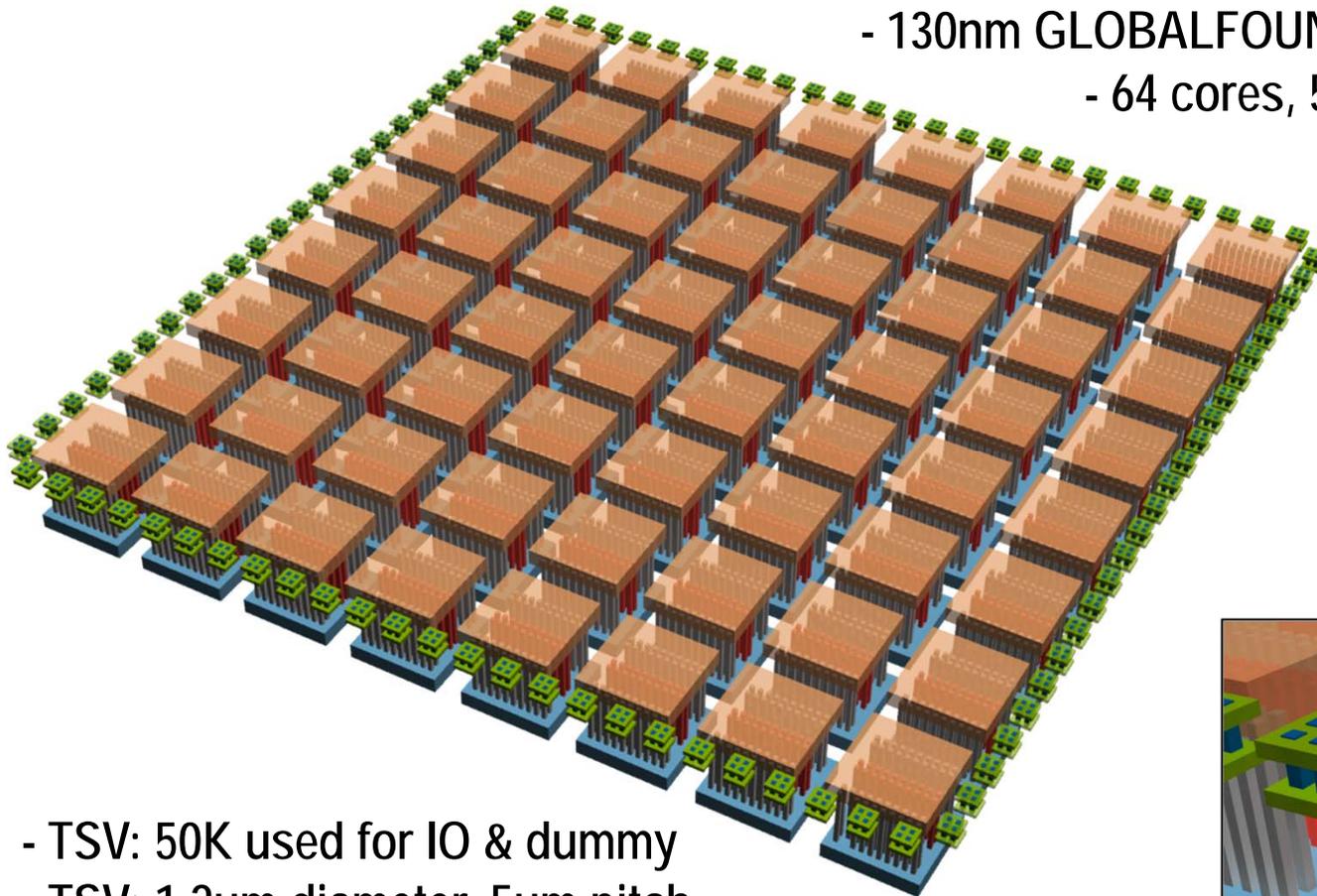
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- Papers on TSV modeling and manufacturing: **many**
- Papers on CAD tools: **some**
- Papers on architecture and application: **few**
- Papers on test chips: **few**
  - Neuromorphic vision chip, Tohoku Univ [ISSCC'01]
  - Inductive coupling, Keio Univ [ISSCC'08]
  - DDR3 DRAM, Samsung [ISSCC'09]
  - Design-for-Reliability, IMEC [ISSCC'10]
  - Wide-I/O DRAM, Samsung [ISSCC'11]
- **Objective: build the first general-purpose many-core 3D processor**

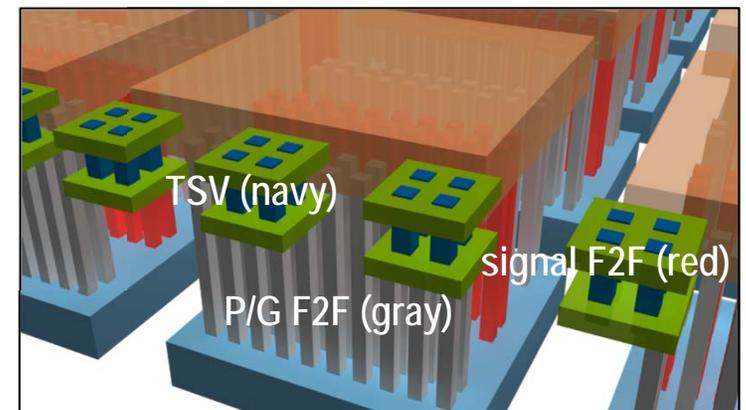
# 3D-MAPS: An Overview

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- 3D **MA**ssively **P**arallel processor with **S**tacked memory
- 130nm GLOBALFOUNDRIES + Tezzaron F2F bonding
- 64 cores, 5-stage/2-way VLIW architecture
- 256KB SRAM, 1-cycle access
- 5mm X 5mm, 230 IO cells
- 277MHz Fmax, 1.5V Vdd
- **64GB/s memory BW @ 4W**



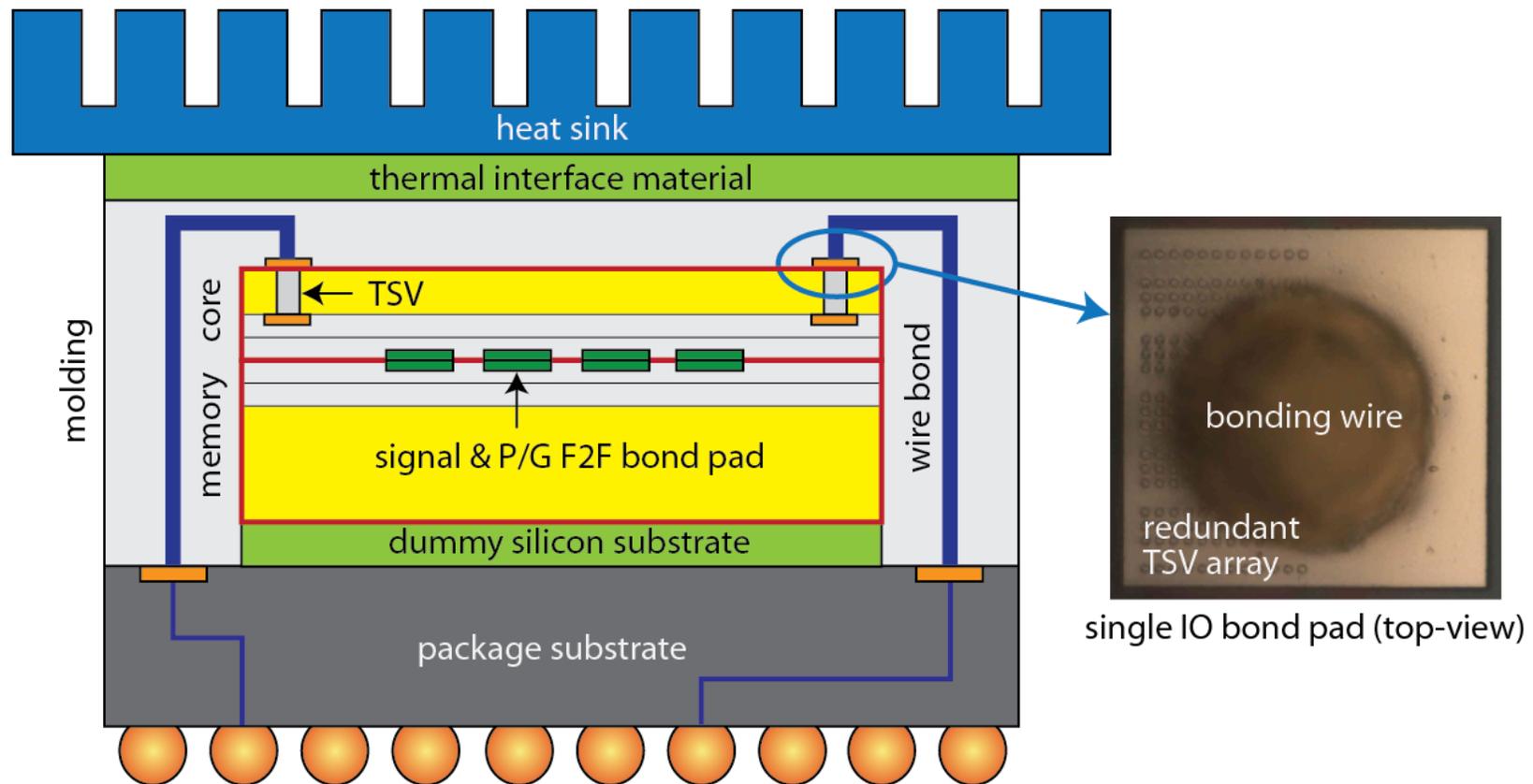
- TSV: 50K used for IO & dummy
- TSV: 1.2um diameter, 5um pitch
- F2F: 50K used for memory access
- F2F: 3.4um diameter, 5um pitch



# Tezzaron 3D Stack-up

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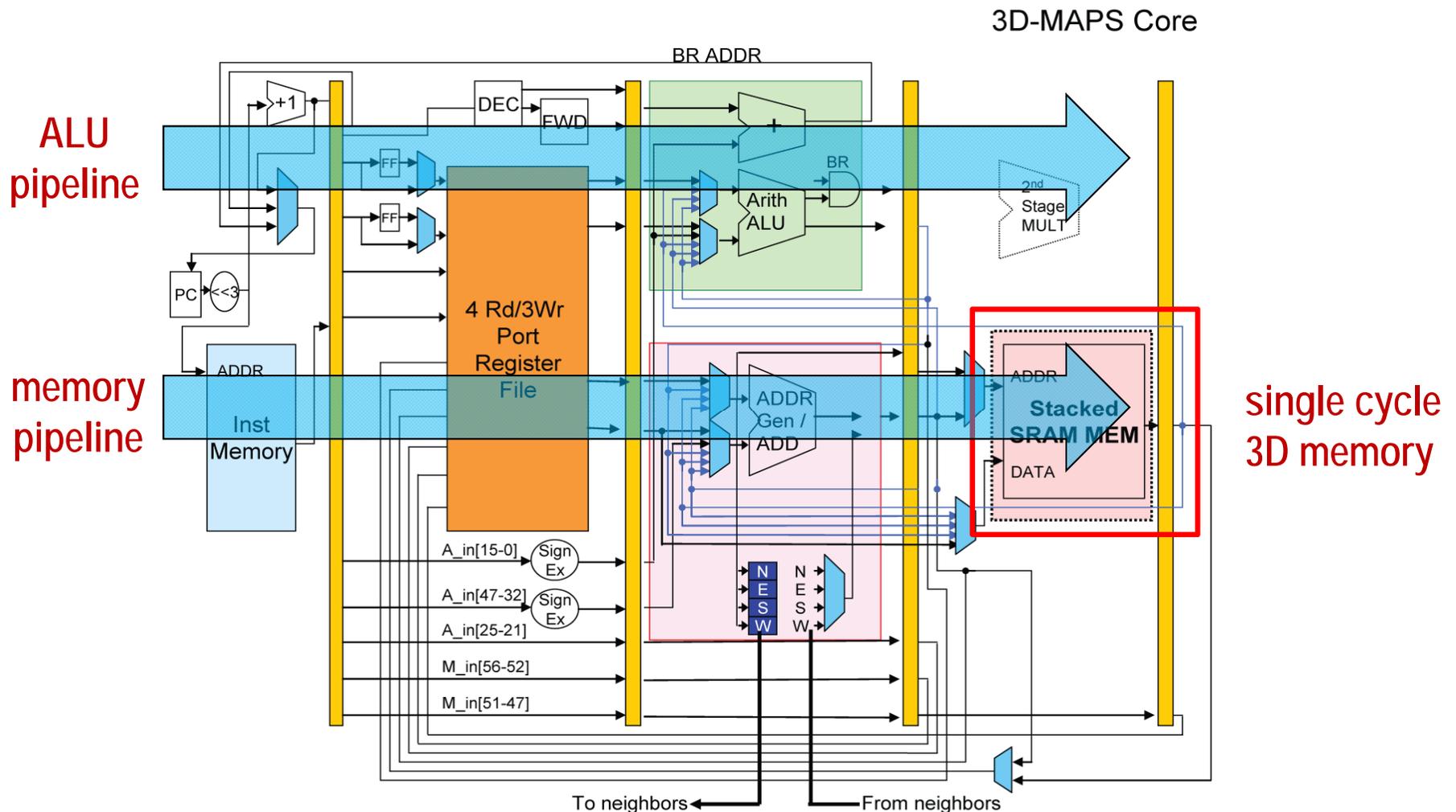
- 2 logic tiers, face-to-face bonded
  - Top die thinned to 12um, bottom die is 765um
  - GLOBALFOUNDRIES 130nm technology + Artisan library/IP



# 3D MAPS Core Architecture

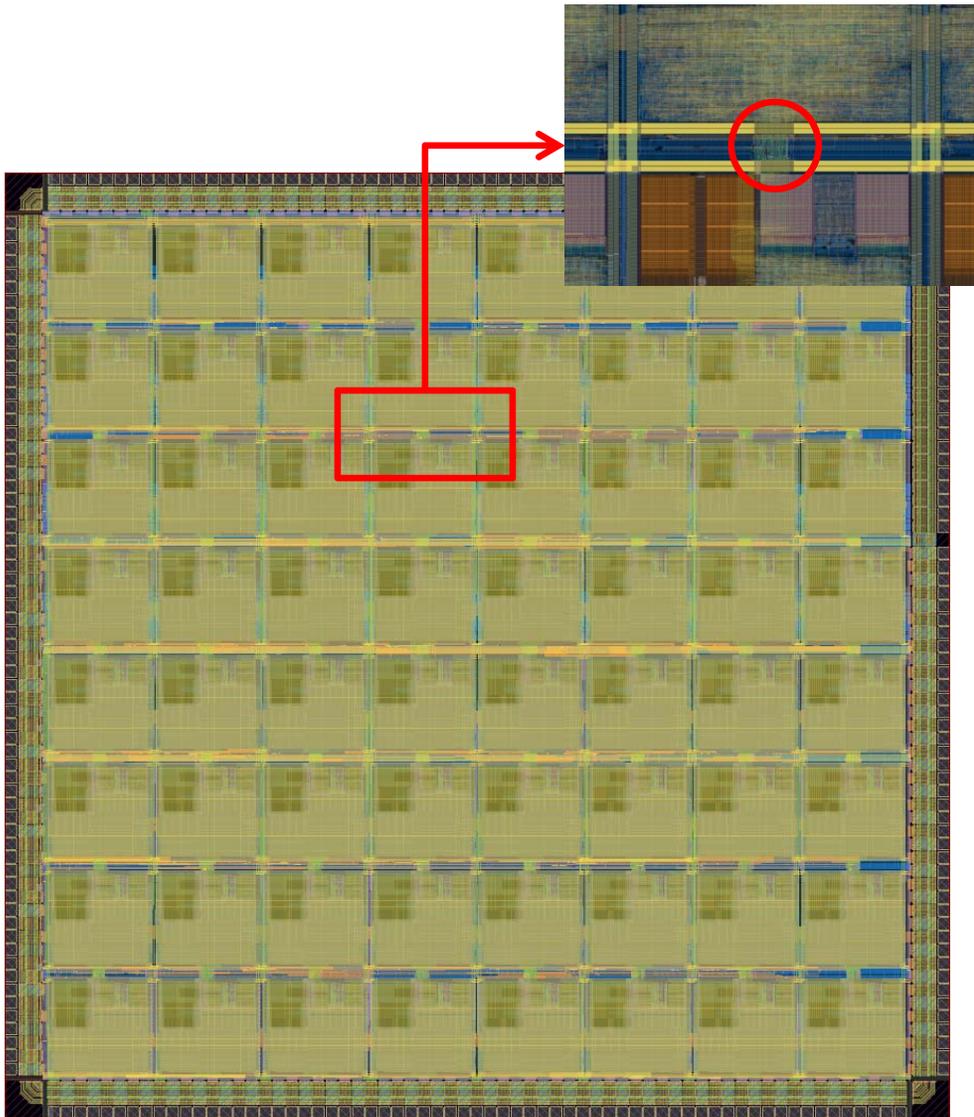
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- 2-issue (memory/ALU), 5-stage VLIW
  - single cycle memory access at every cycle

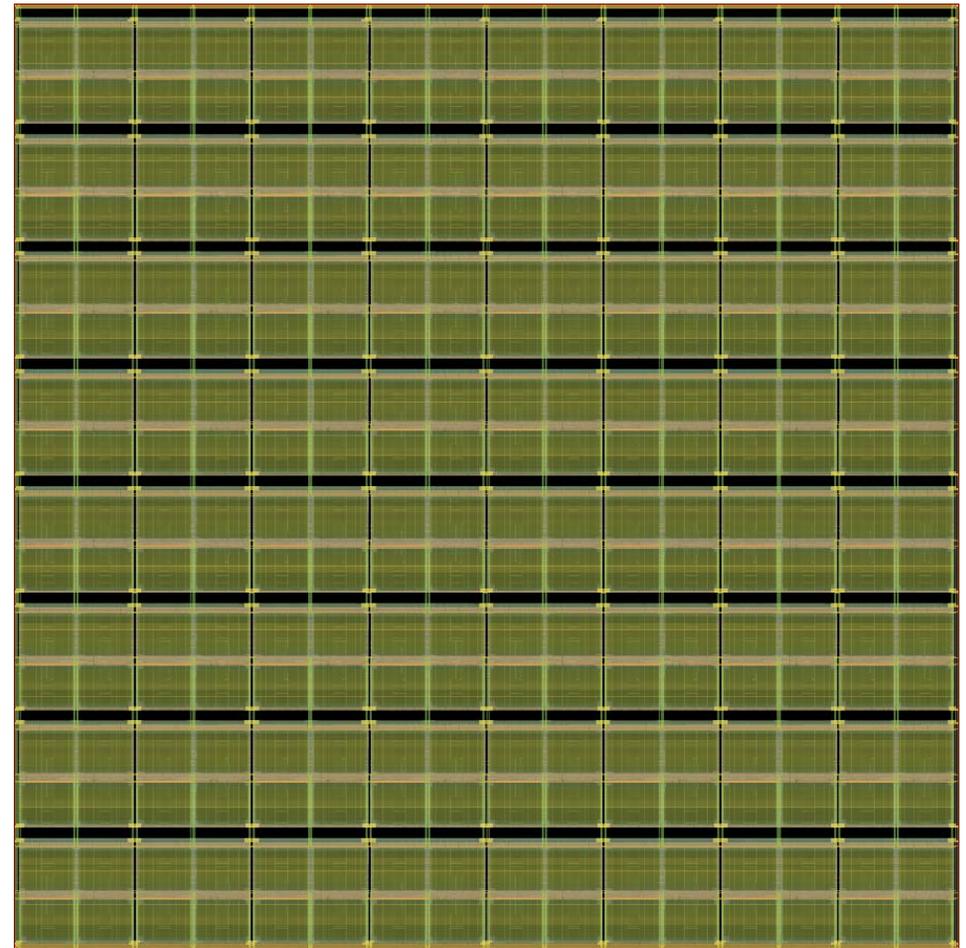


# V1 Full-die Layouts

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core-to-core wires

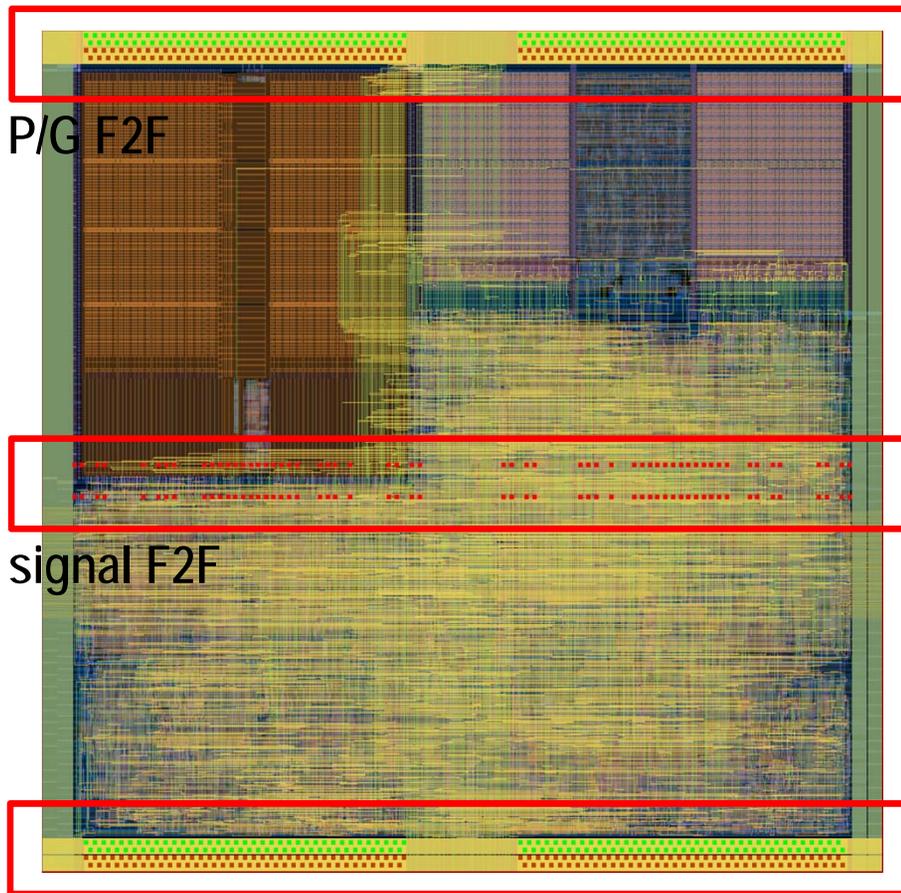


64 cores + 235 IO cells (on periphery)

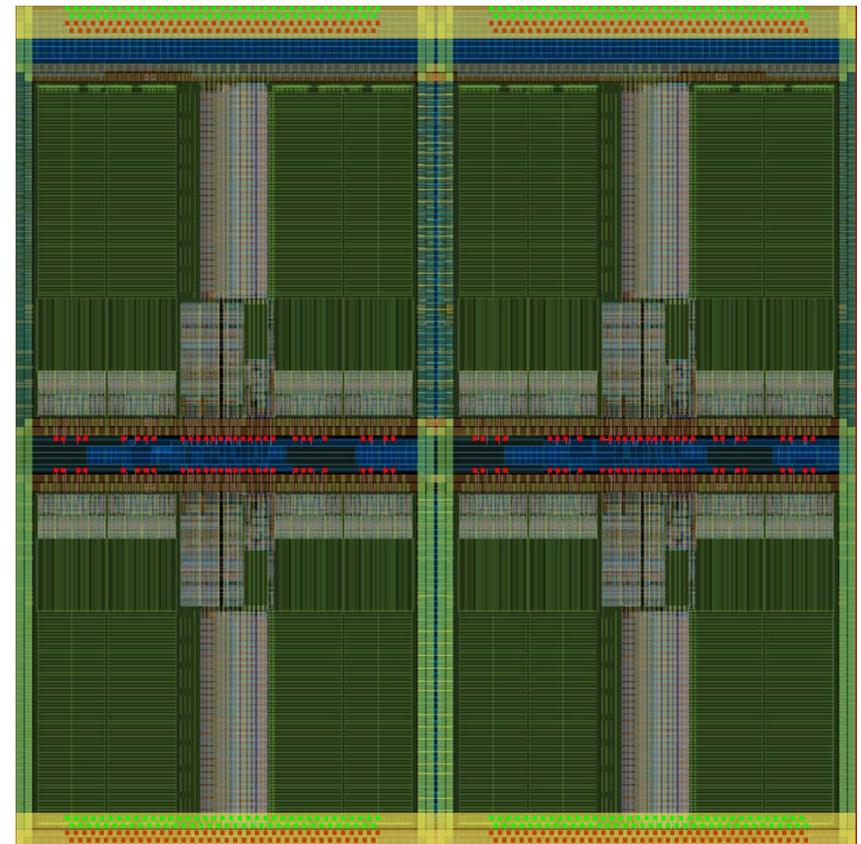
64 SRAM memory tiles (64 x 4KB)

# Face-to-face Via Usage

- Spec: 3.4um diameter, 5um pitch, negligible RC
  - Usage: 64 for signal, 684 for P/G per core



P/G F2F      single core

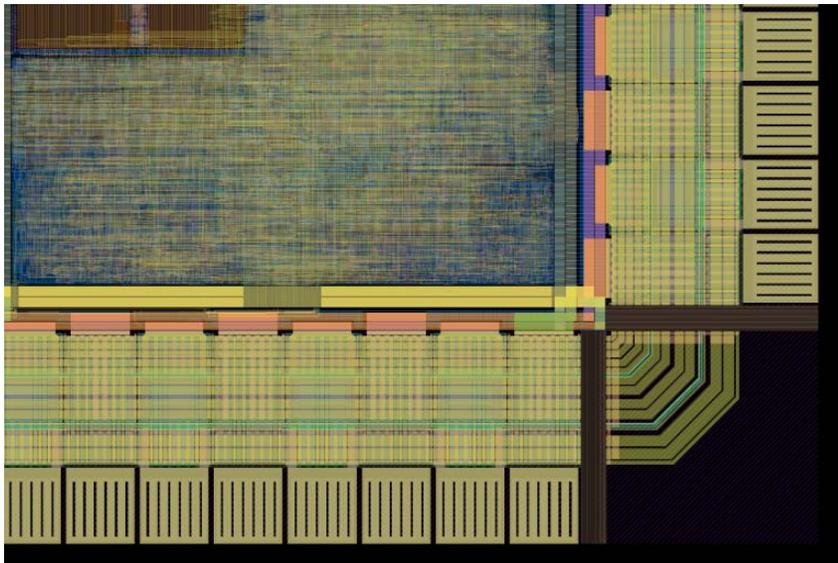


single SRAM tile (4KB)

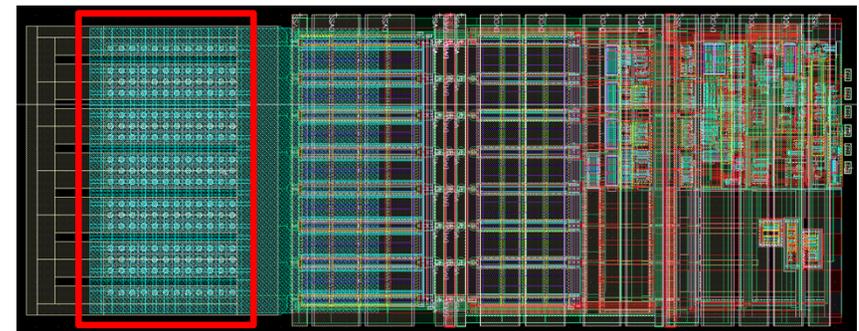
# Through-Silicon-Via Usage

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- Spec: 1.2um diameter, 5um pitch,  $R = 0.6\text{ohm}$ ,  $C = 3\text{fF}$ 
  - Usage: mainly in IO cells
  - 204 redundant TSVs in each IO cell
  - 53 dummy TSVs per core



IO cells along the periphery

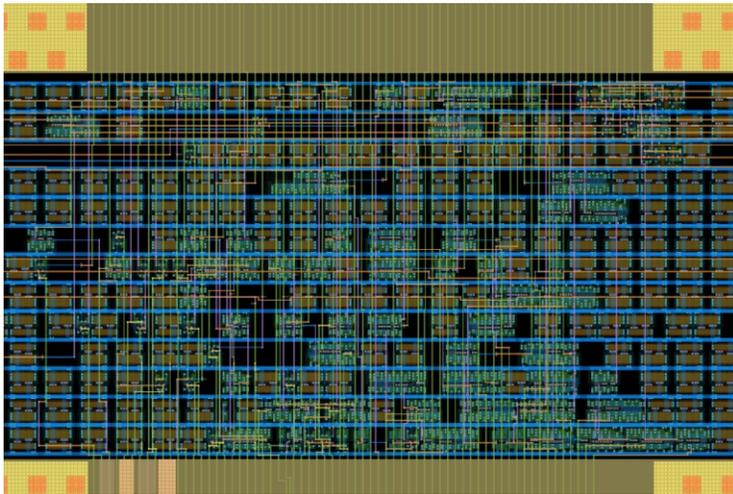


12x17=204  
P/G TSV array

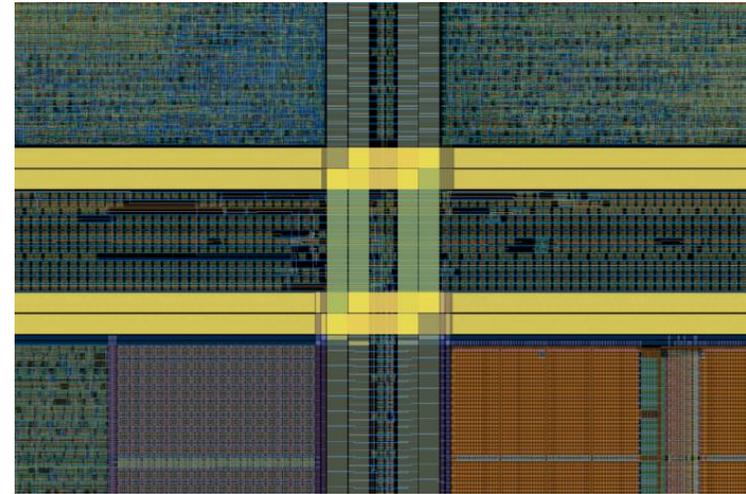
IO cell (zoom-in)

# Timing Closure and Power Delivery

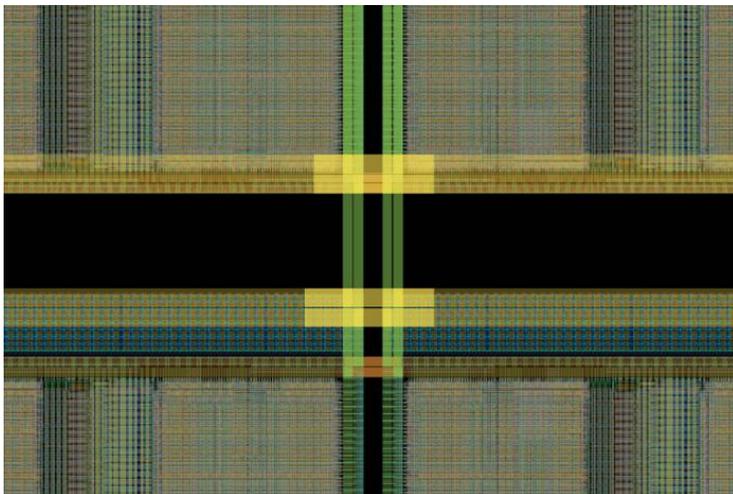
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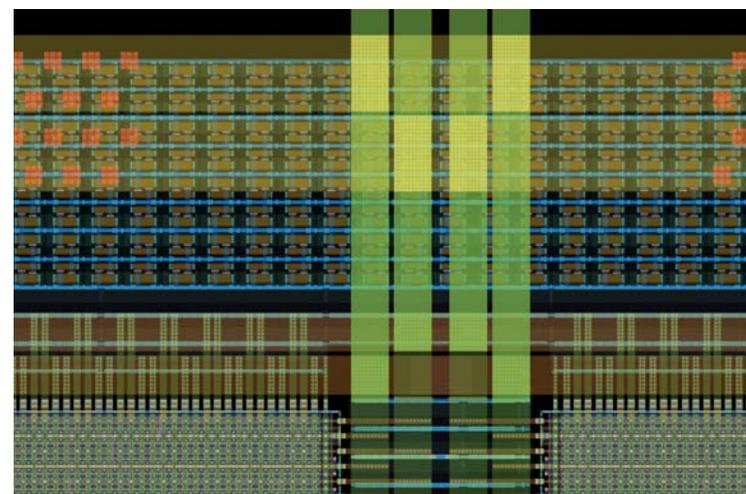
buffers and gates in between cores



P/G rings for the cores



P/G rings for SRAM tiles



decap cells attached to P/G rings

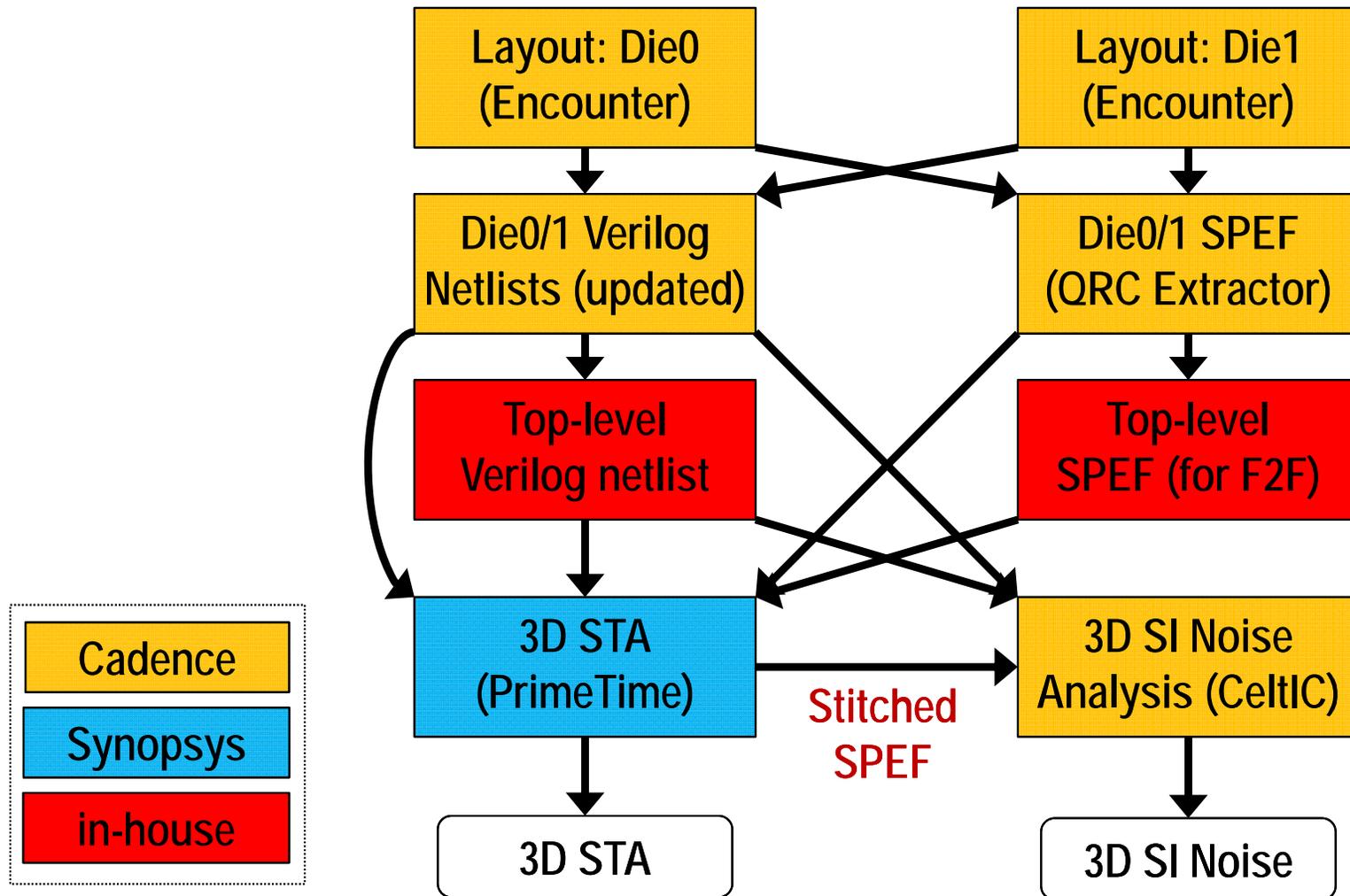
# 3D CAD Tools and Methodologies

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- Commercial 3D tools are **NOT** available
- We started with 2D Tools and added scripts & plug-ins
  - 3D layout construction: Encounter
  - 3D timing optimization: Encounter + PrimeTime
  - 3D timing and SI analysis: CeltIC + PrimeTime
  - 3D power analysis: ModelSim + Encounter
  - 3D clock analysis: Encounter + SPICE
  - 3D IR-drop analysis: VoltageStorm
  - 3D thermal analysis: ANSYS + Fluent
  - 3D DRC/LVS: Calibre
- Used to design both V1, V2, and more

# 3D Static Timing Analysis with SI

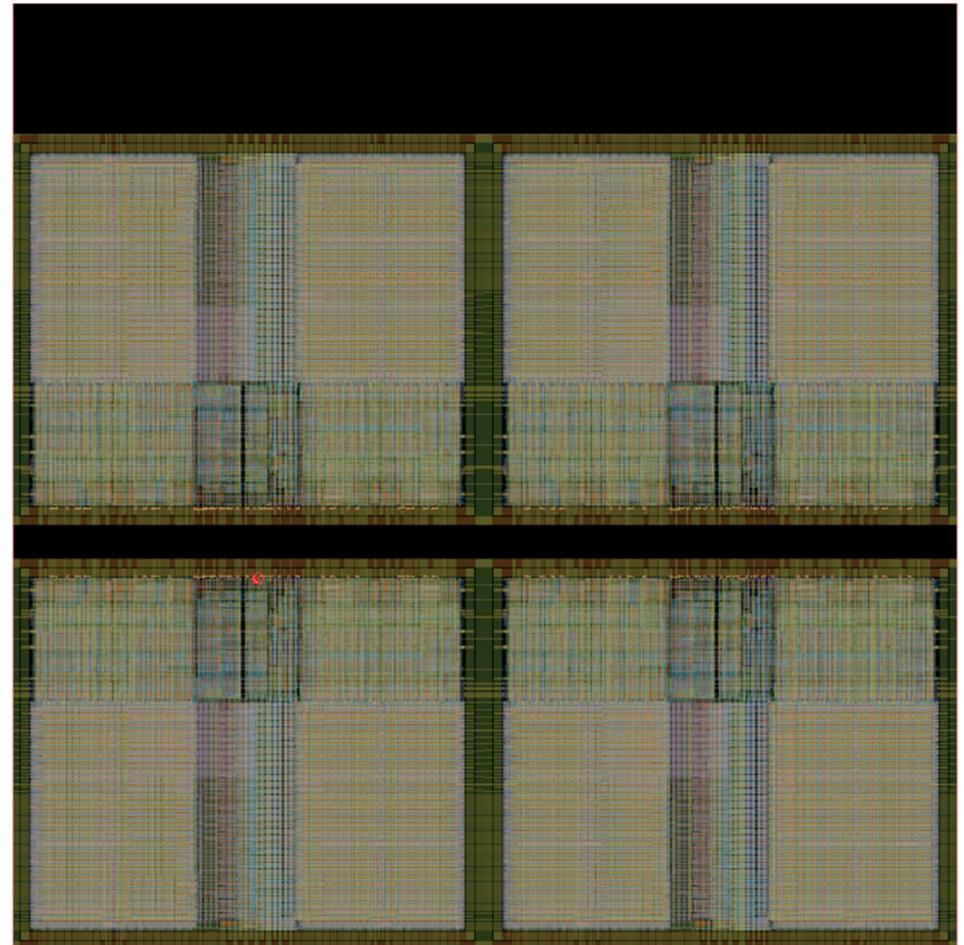
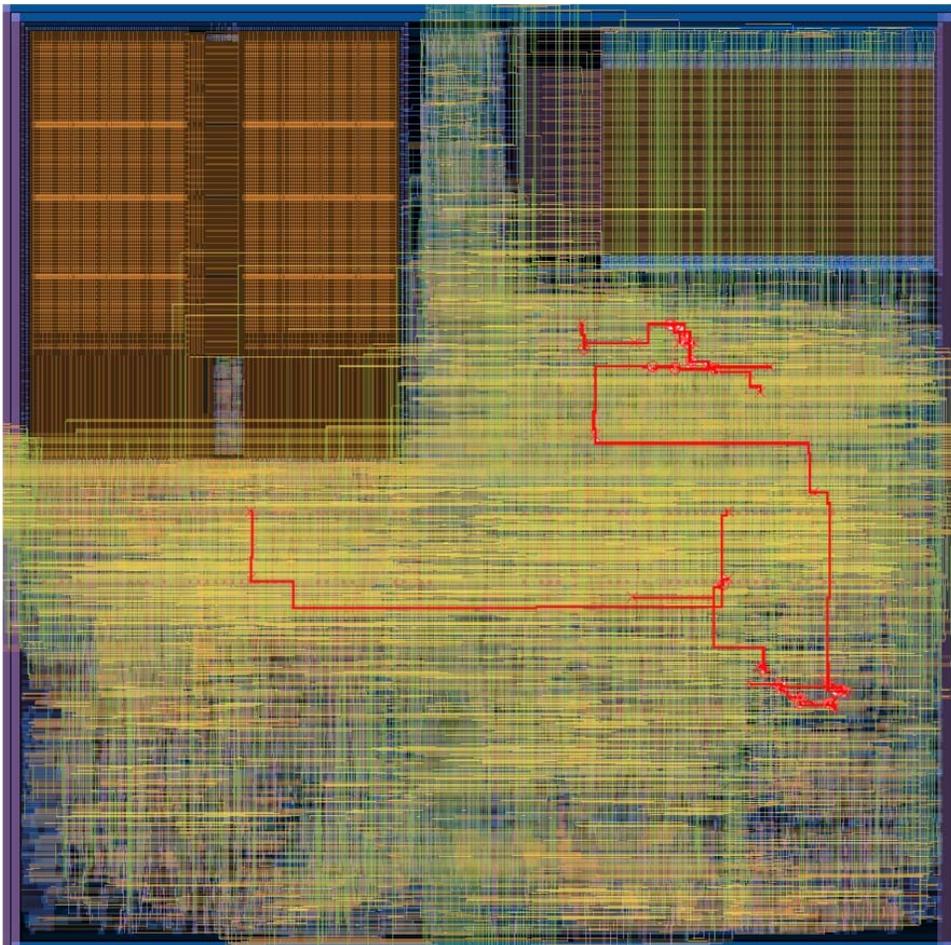
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# 3D Timing Analysis

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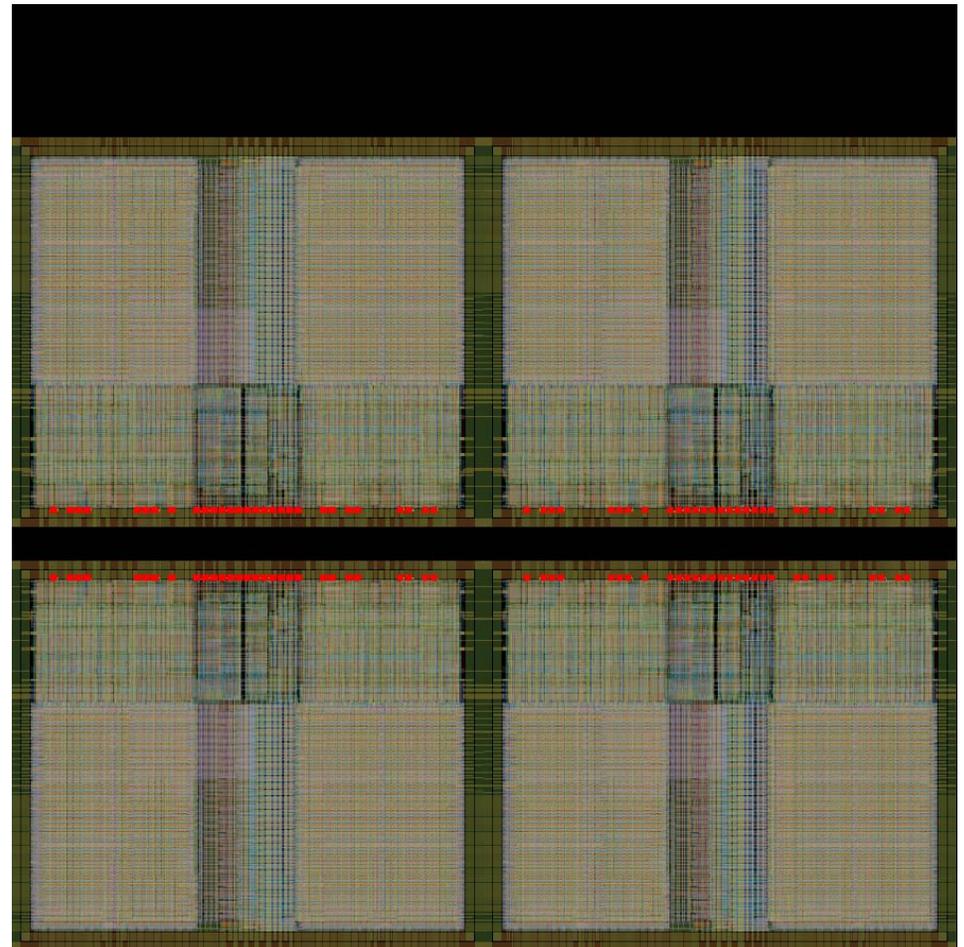
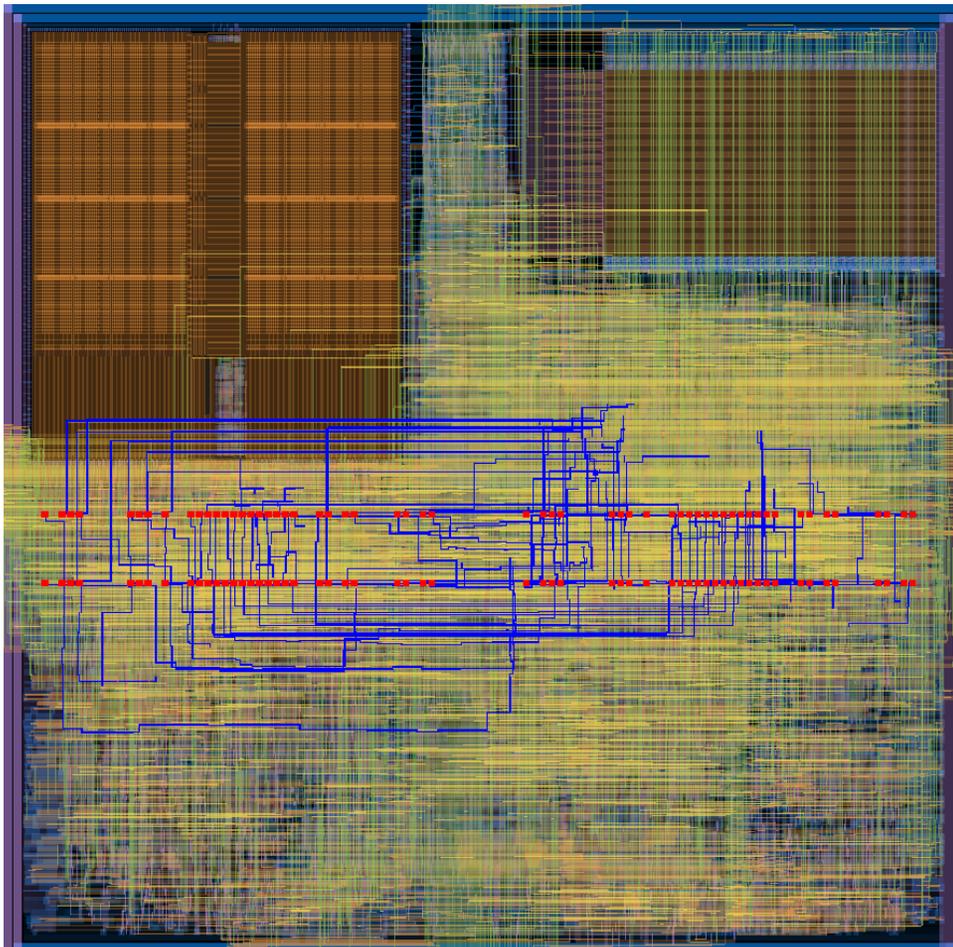
- Our worst-case path has 3.6ns delay, so  $F_{max} = 277\text{MHz}$ 
  - RF-to-memory write path: stage 2/3 FF – MUX – ADD – MUX – DMEM\_ADDR



# 3D Signal Integrity Analysis

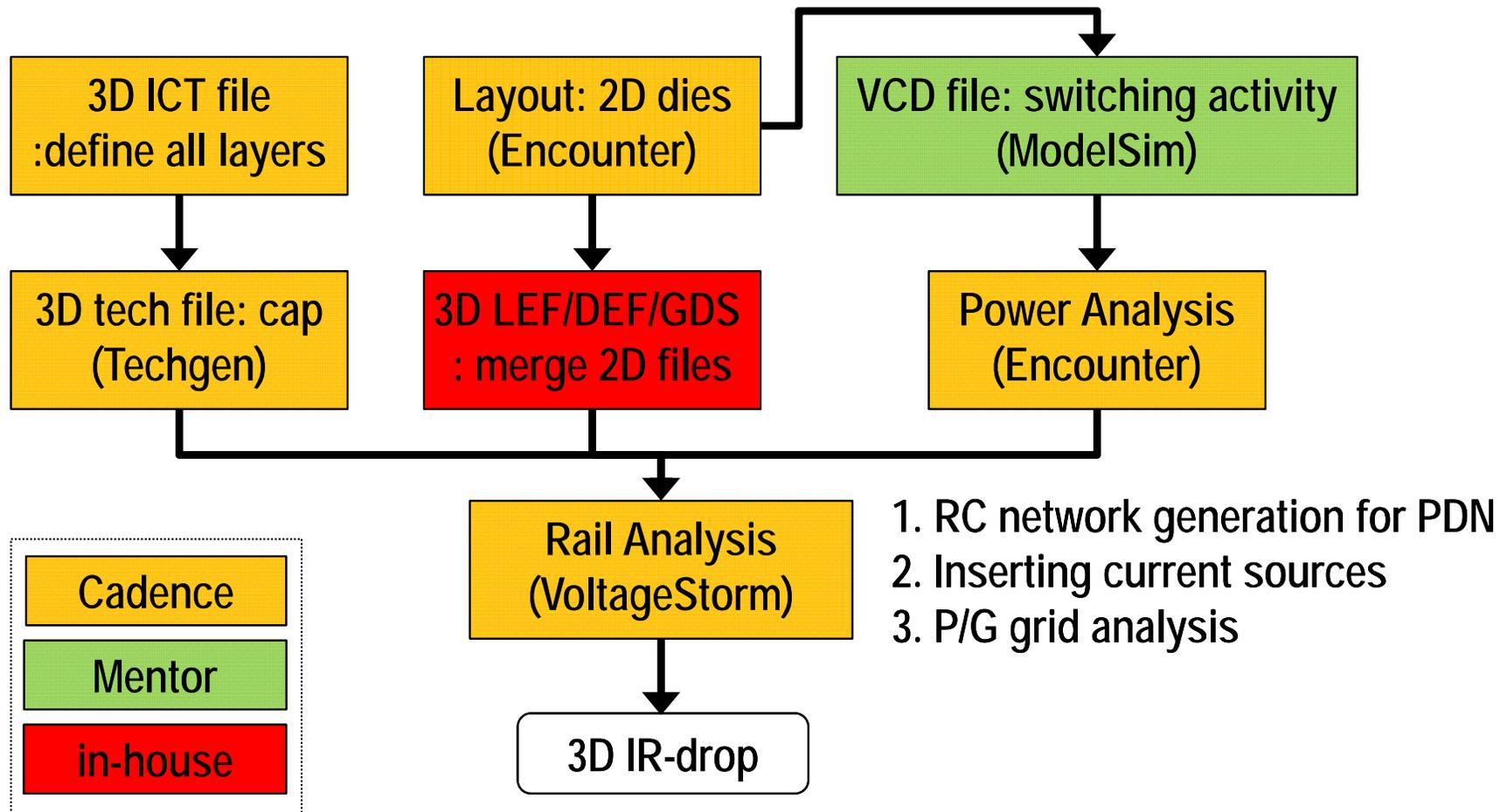
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- We analyze both 2D and 3D nets
  - All nets < 500mV: 5um F2F pitch was enough



# 3D IR-drop Analysis

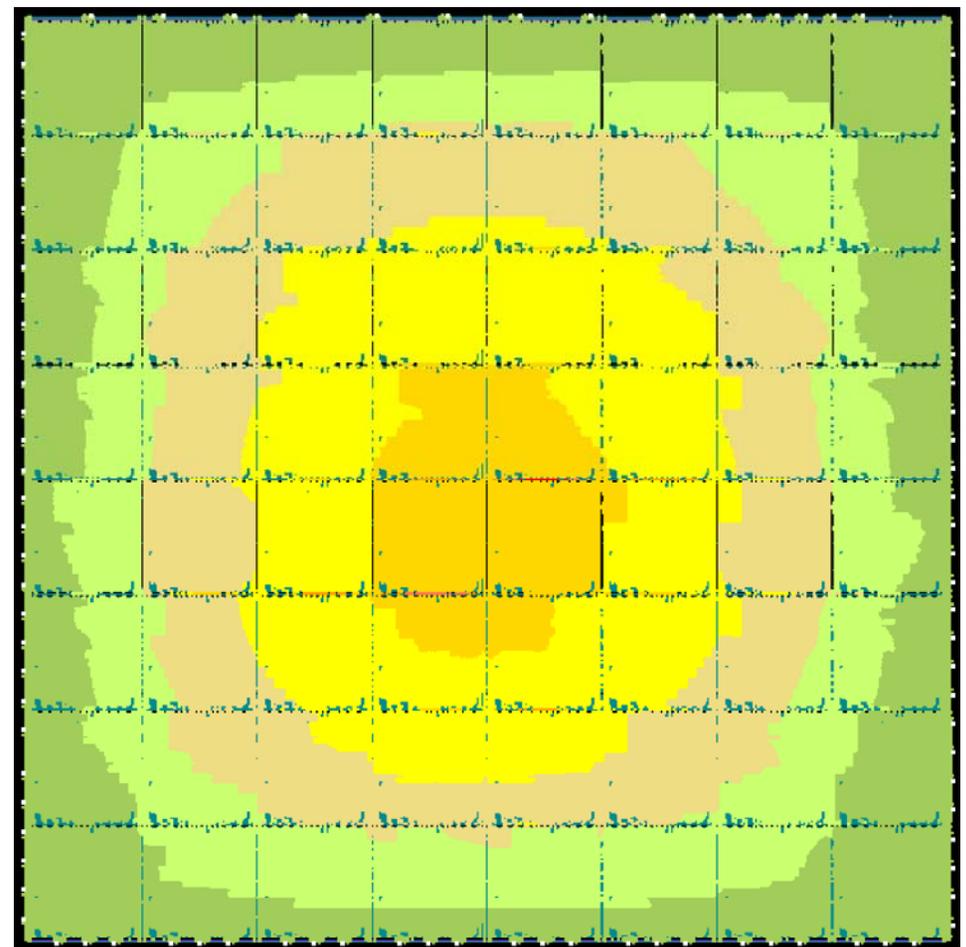
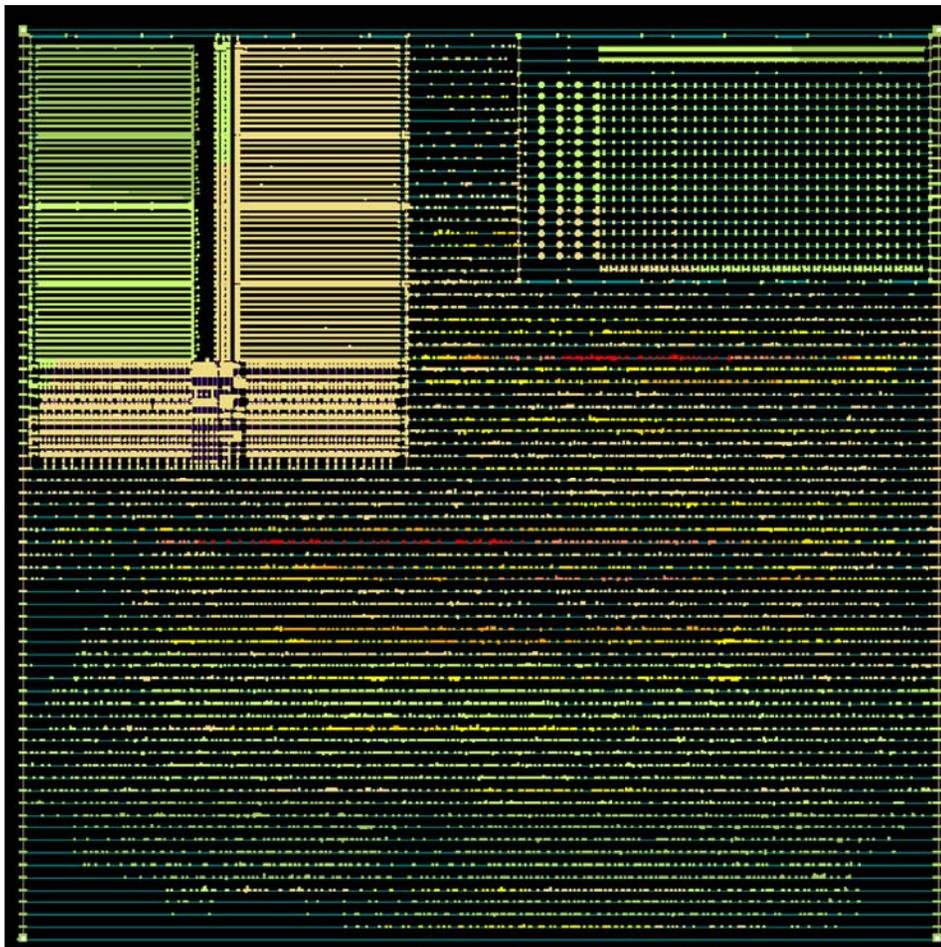
- Can handle di/dt noise as well



# 3D IR-drop Analysis

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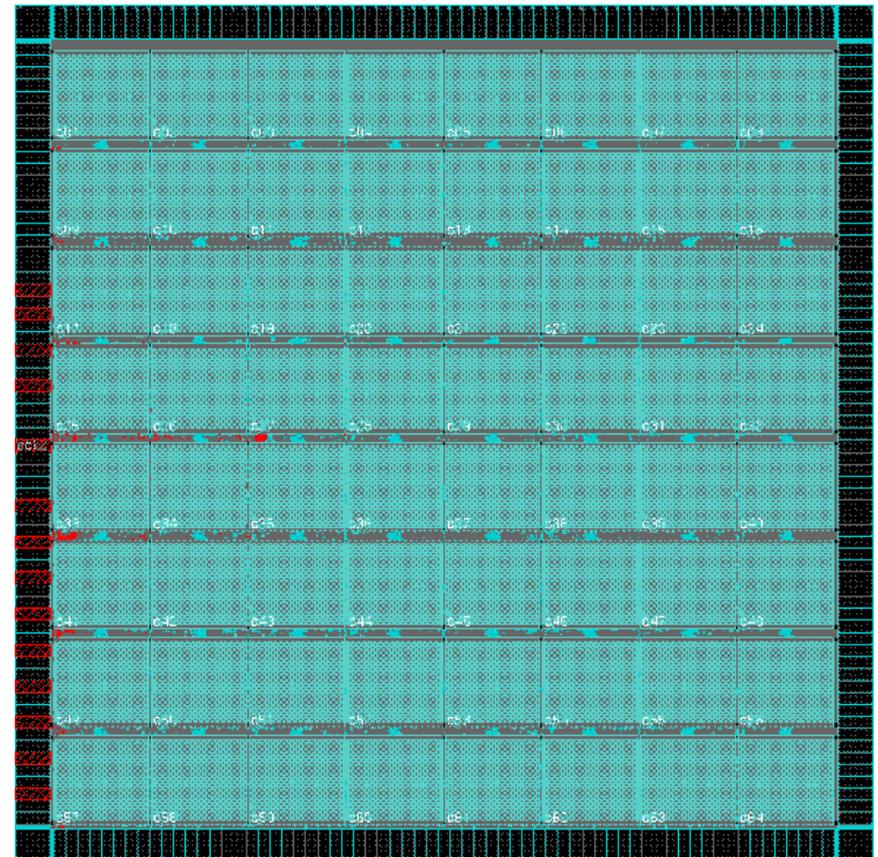
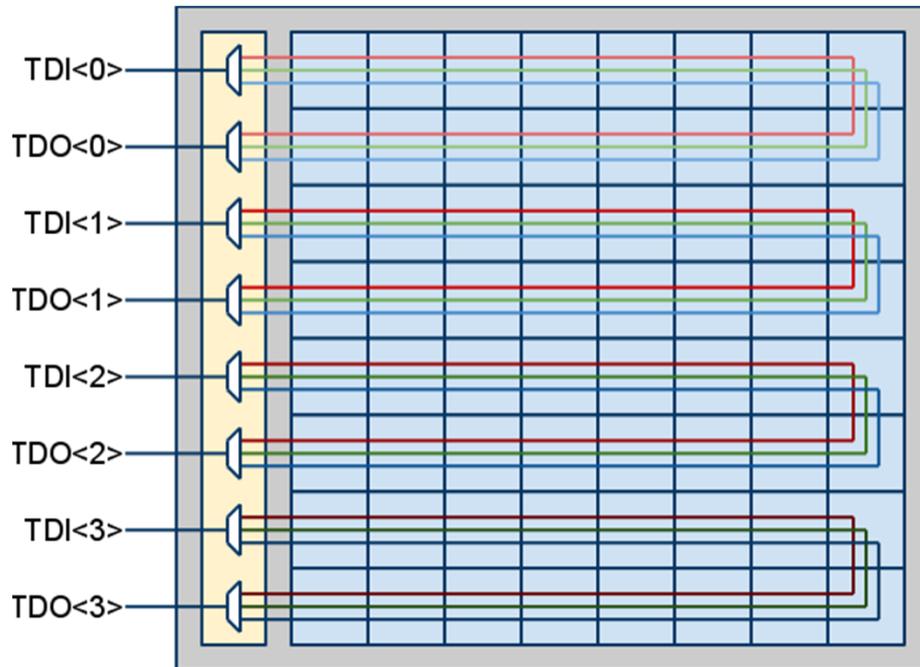
- Single-core: clock buffers are power hungry (60mV)
- 64-core: cores in the middle experience more IR-drop (78mV)



# DFT Infrastructure

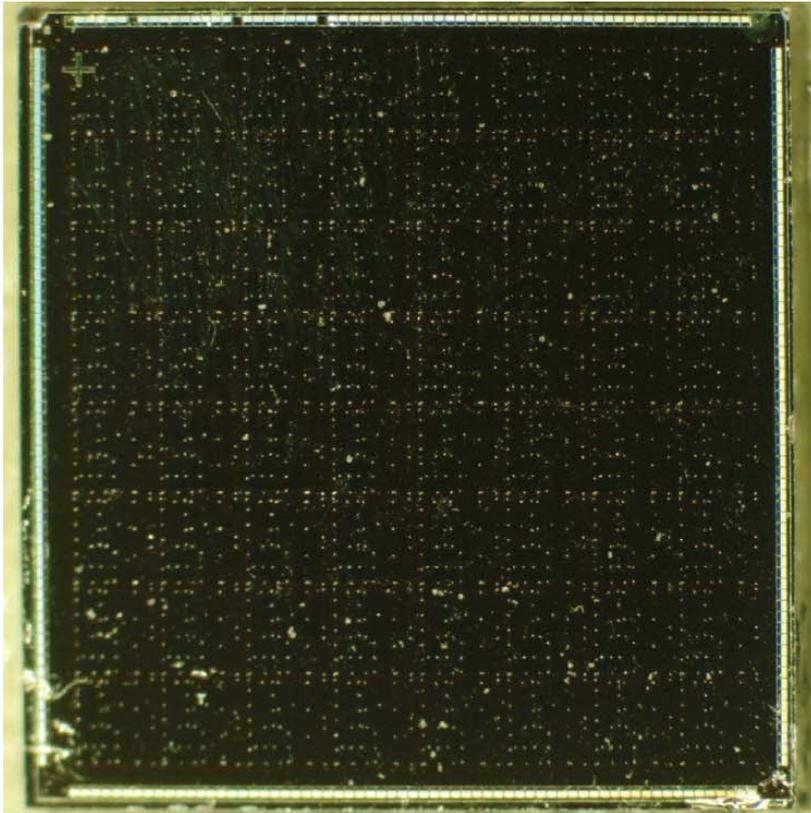
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- 64 cores split into 4 sectors, tested independently
  - Scan IO pins located on one side
  - Testing circuitry sitting in between the cores

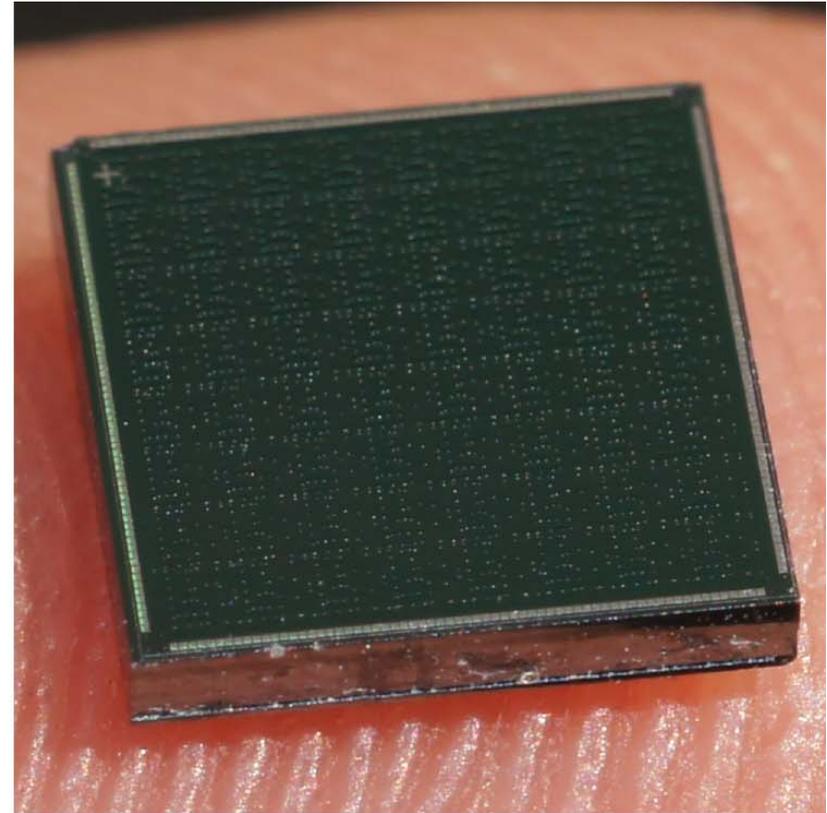


# 3D-MAPS Die Photos

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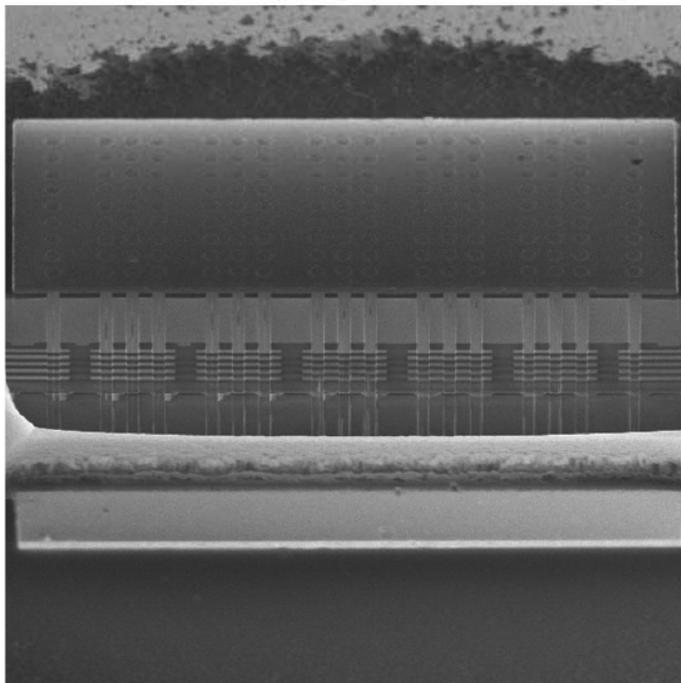
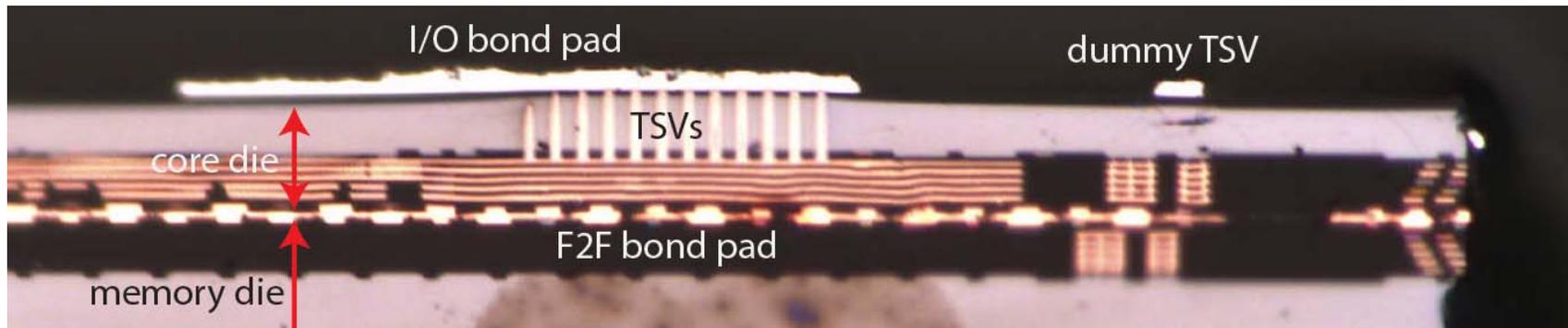


die photo, backside of core (= thinned) die

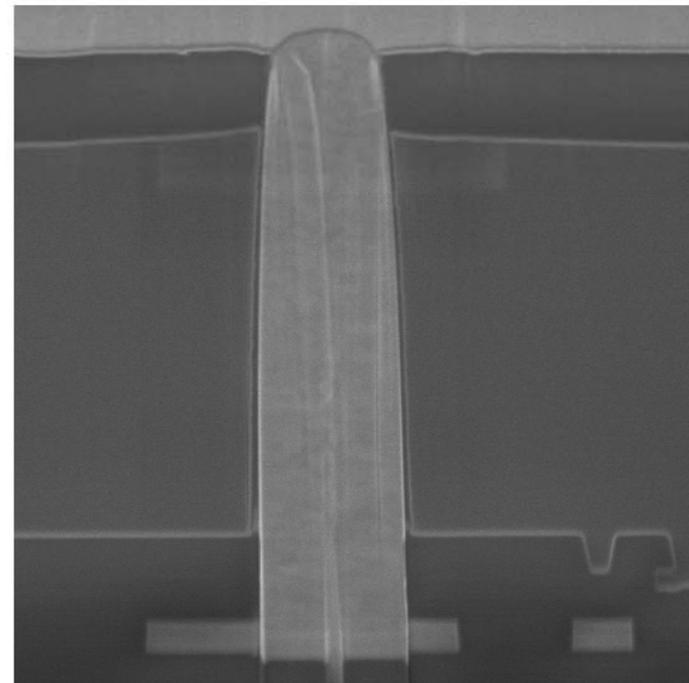


whole die, dummy TSVs, IO cells on periphery

# SEM Images

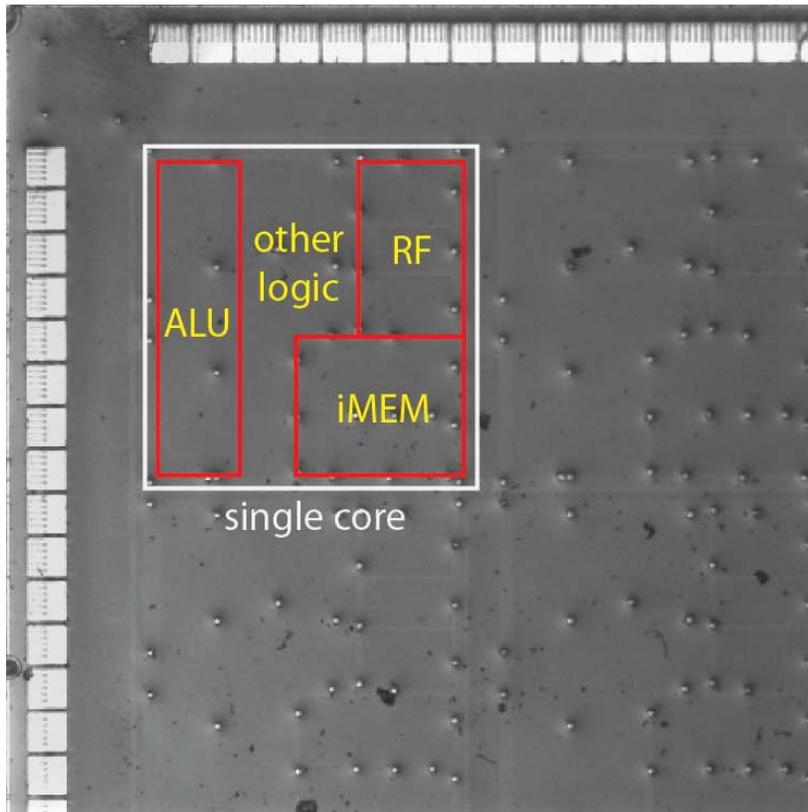


single IO cell, TSVs, BEOL of core die

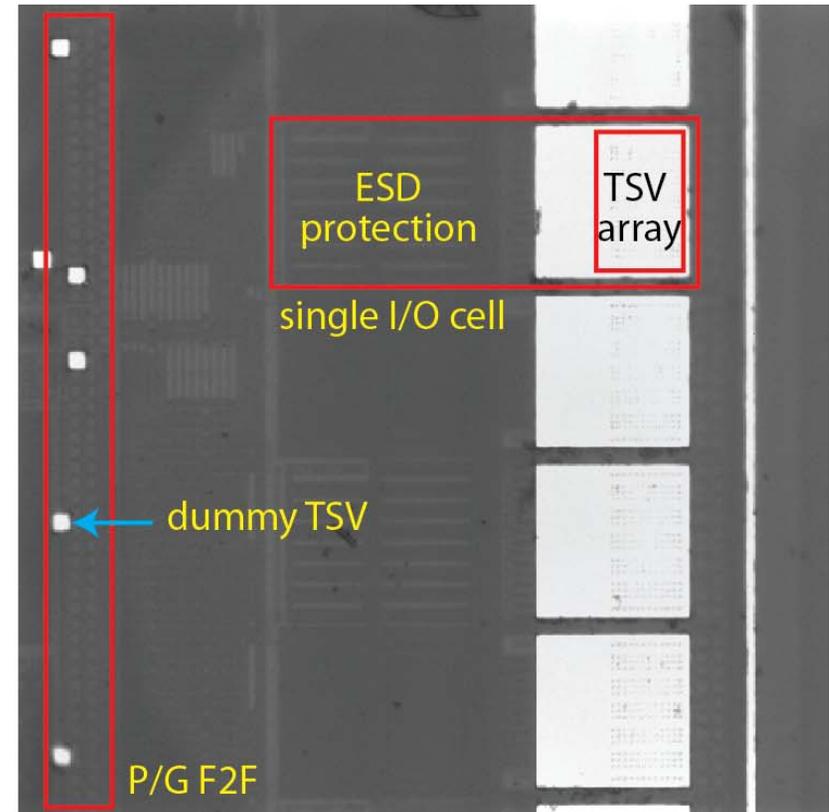


single TSV and its landing pads

# IR Images



I/O cells and cores, IR image w/ 6um depth

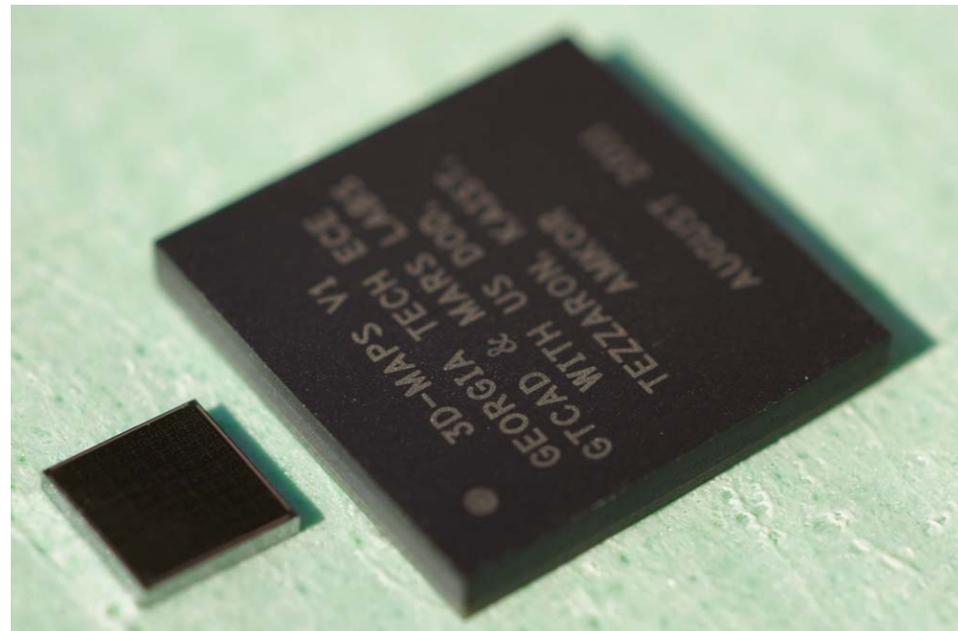
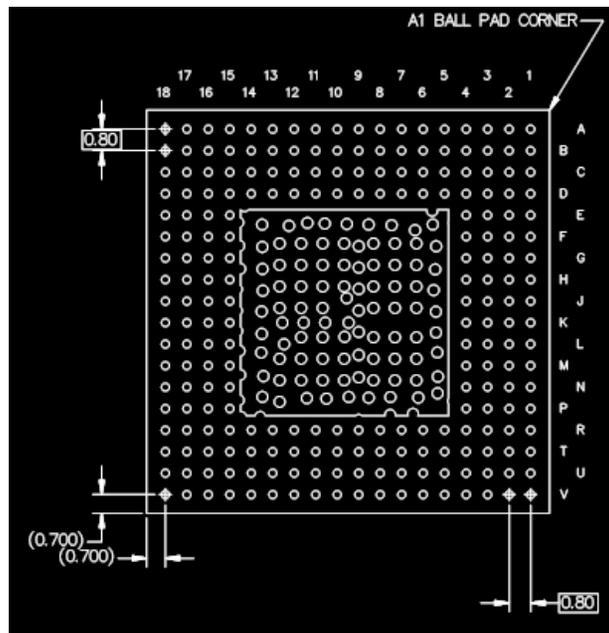
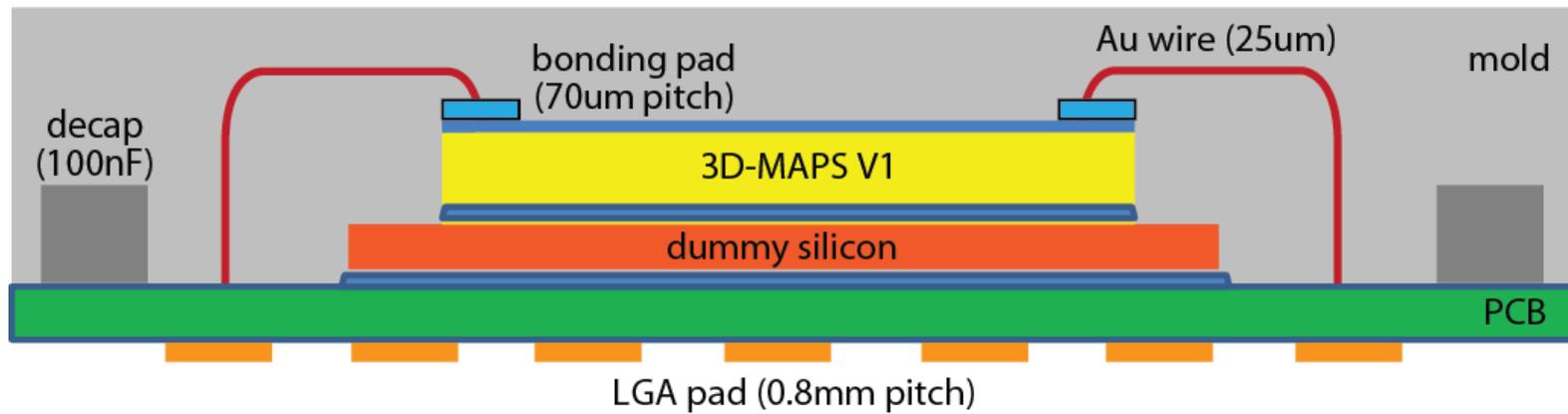


I/O cells ESD circuit, IR image w/ 6um depth

# Amkor Packaging

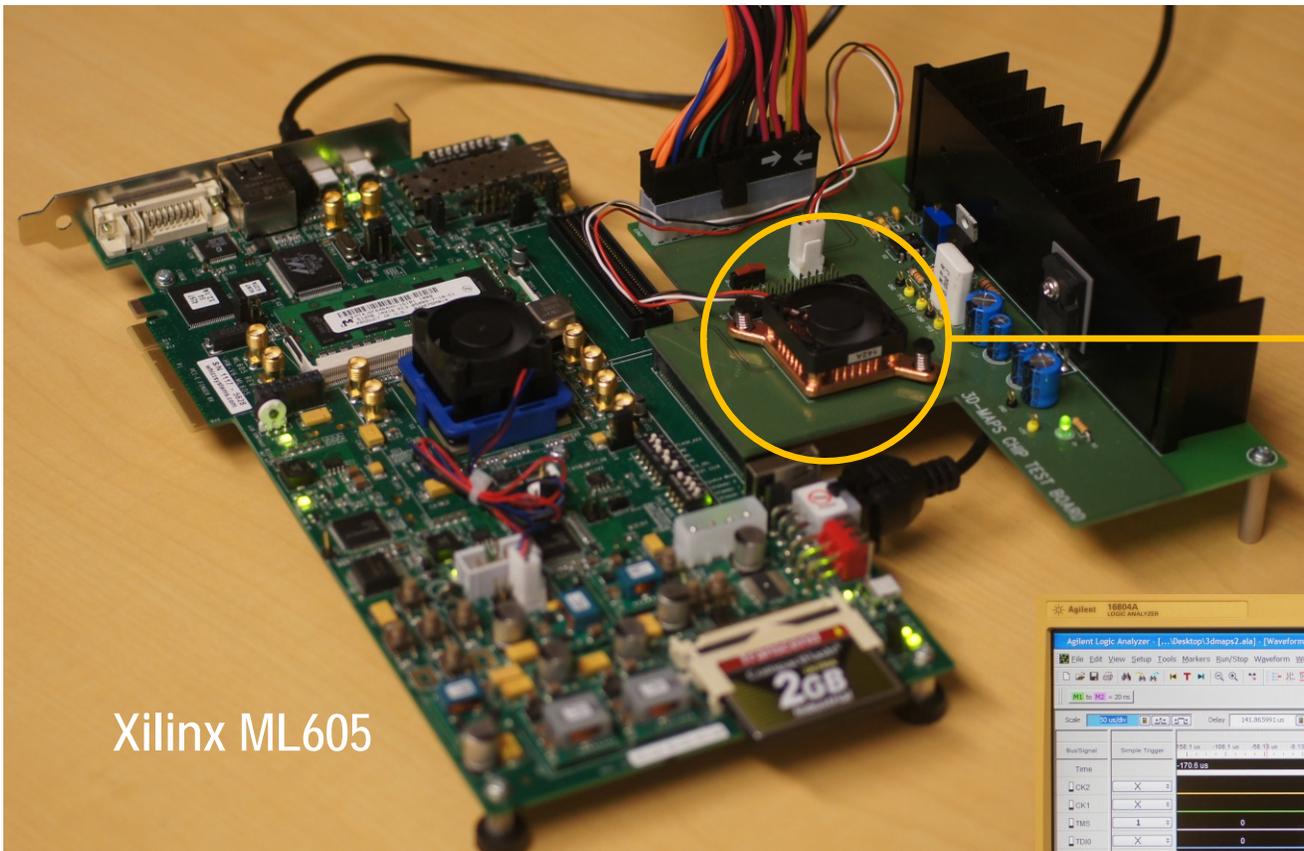
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15mm X 15mm



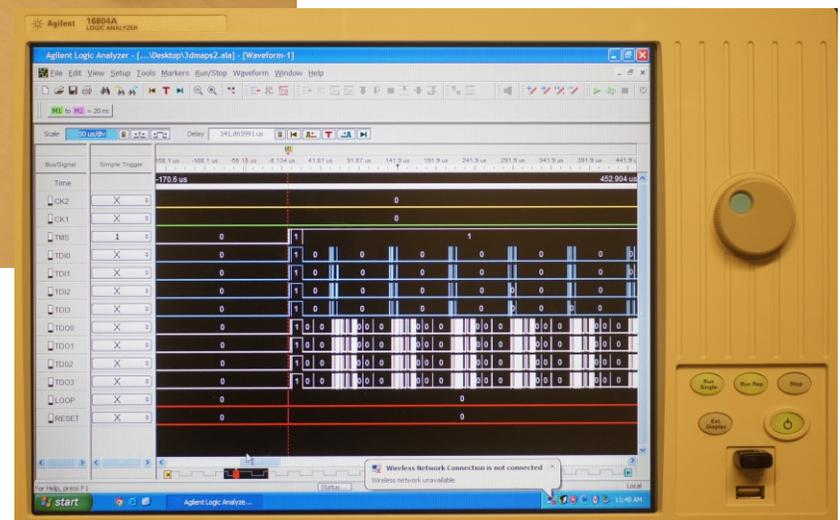
# Testing Infrastructure

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3D-MAPS V1

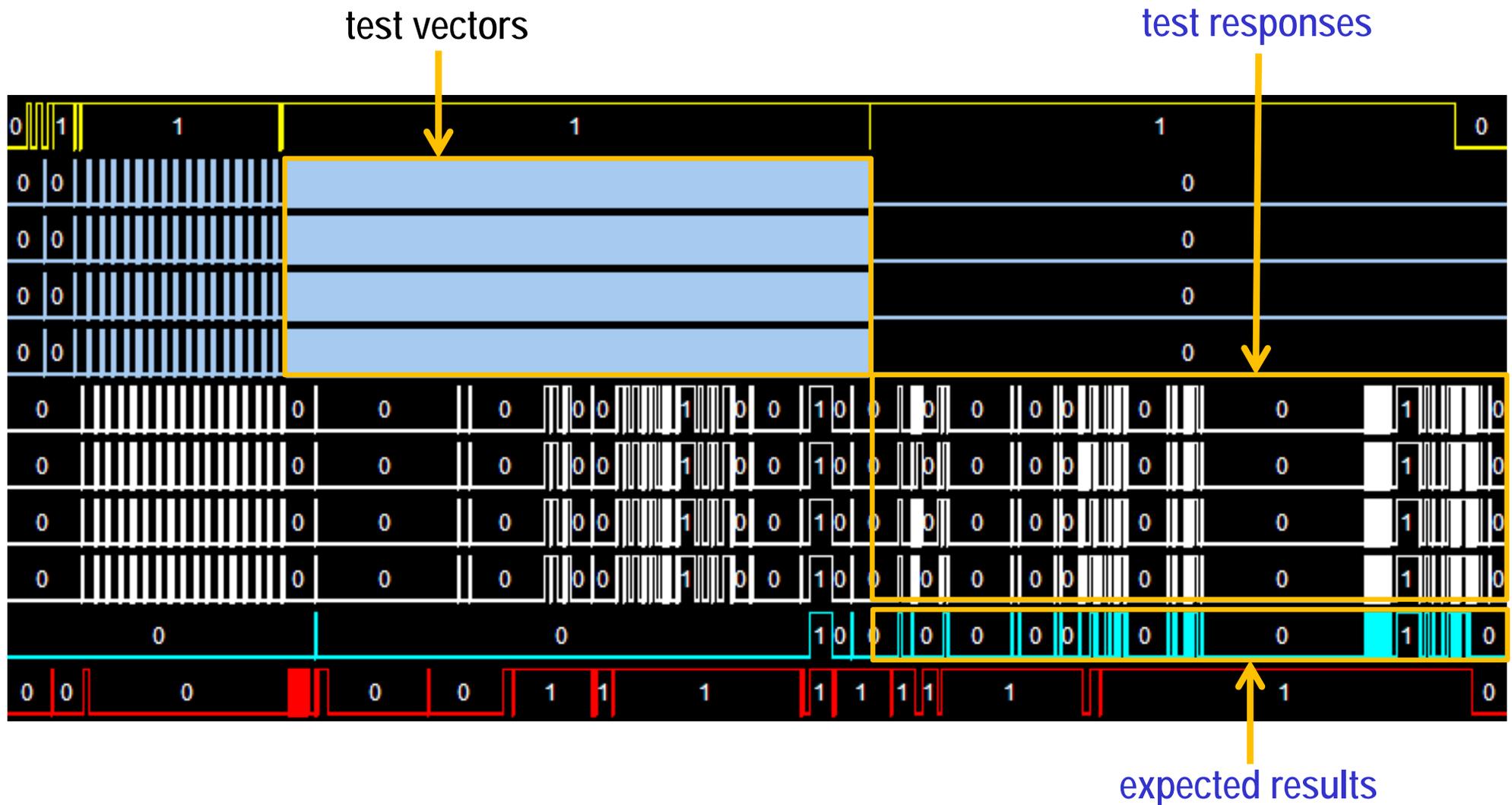
Xilinx ML605



Agilent 16804A

# Sample Bit Stream: 3D Interface Test

- Data memory R/W works: **TSVs and F2Fs work**





# BW and Power Measurement

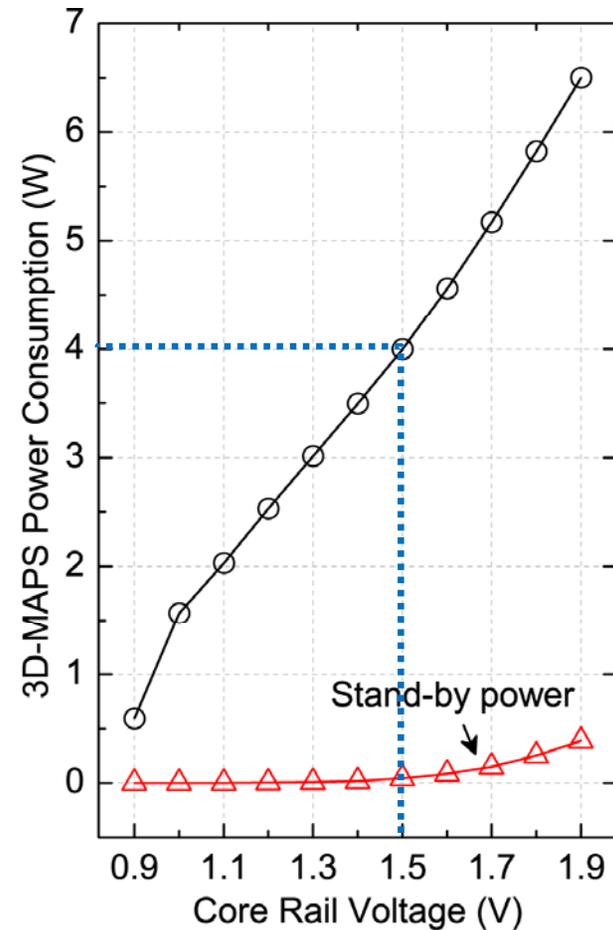
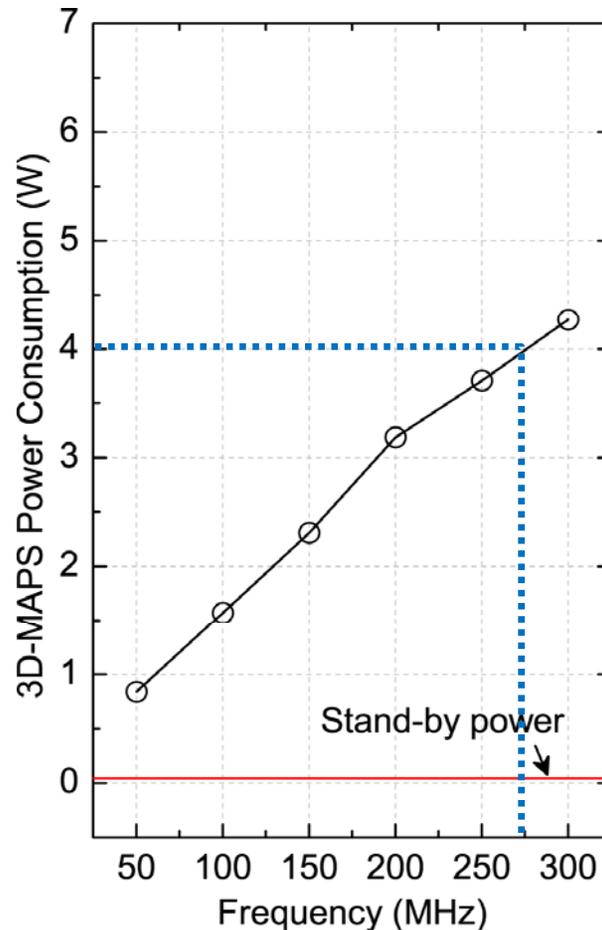
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- 64-core version of apps written in assembly
  - 3D-MAPS V1 supports **42 integer instructions**
  - Max achievable BW is  $277 \text{ MHz} \times 64 \text{ ch} \times 4 \text{ Bytes} = \mathbf{70.9 \text{ GB/s}}$
  - **Modern CPU + DDR3 BW: 25 to 30GB/s**

benchmark	Memory bandwidth	Measured Power
AES encryption	49.5 GB/s	4.032 W
Edge detection	15.6 GB/s	3.768 W
Histogram	30.3 GB/s	3.588 W
K-means clustering	40.6 GB/s	4.014 W
Matrix multiply	13.8 GB/s	3.789 W
<b>Median filter</b>	<b>63.8 GB/s</b>	<b>4.007 W</b>
Motion estimation	24.1 GB/s	3.830 W
String search	8.9 GB/s	3.876 W

# Frequency and Voltage Sweep

- Frequency vs power (voltage = 1.5V)
- Voltage vs power (frequency = 250MHz)



# Ongoing Work: 3D-MAPS V2

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- Through MOSIS/Tezzaron 3D IC MPW (taped out: Oct 2011)

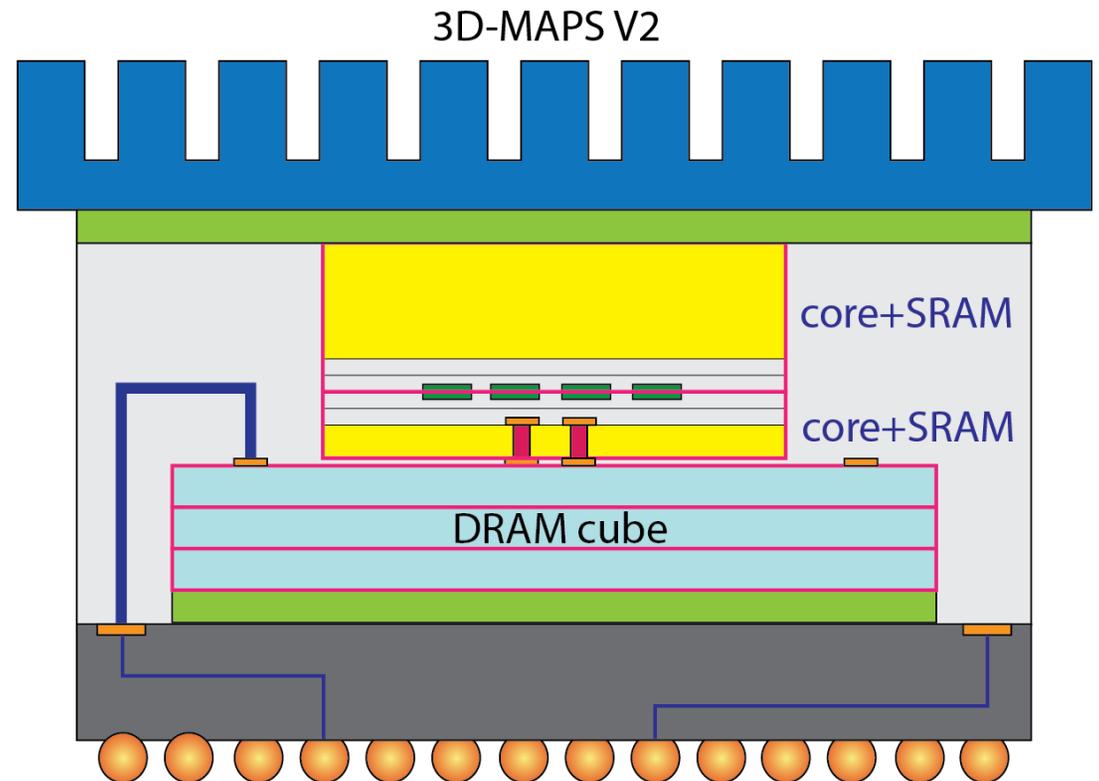
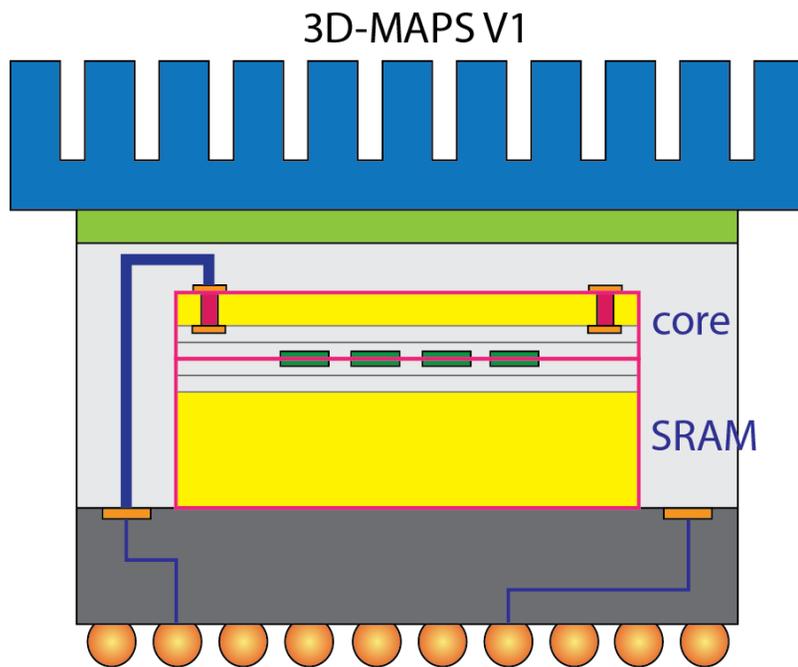
	3D-MAPS V1	3D-MAPS V2
# of tiers	2 (1 logic, 1 SRAM)	5 (2 logic, 3 DRAM)
# of cores	64	128
Memory capacity	256KB SRAM	256MB DRAM & 512KB SRAM
Logic footprint	5mm X 5mm	10mm X 10mm
DRAM footprint	-	20mm X 12mm
Bonding style	F2F	F2F and F2B
TSV/F2F usage	~ 50K / ~50K	~ 150K / ~185K
Memory access*	2048 bit/cycle SRAM	4096 bit/cycle SRAM 2048 bit/cycle DRAM (DDR)
freq / power	277MHz / 4.0W	175MHz / 10.4W

\* Current wide-I/O allows 512 bit/cycle DRAM access

# Stack Up Comparison

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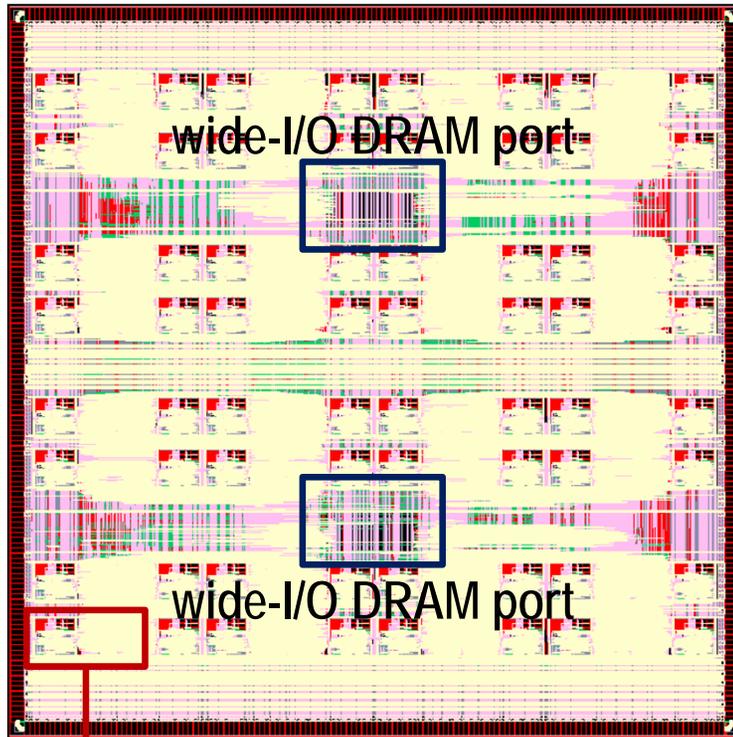
- TSV usage
  - 3D-MAPS V1: For I/O (204 redundancy)
  - 3D-MAPS V2: For I/O (204 redundancy) and DRAM access (9 redundancy)



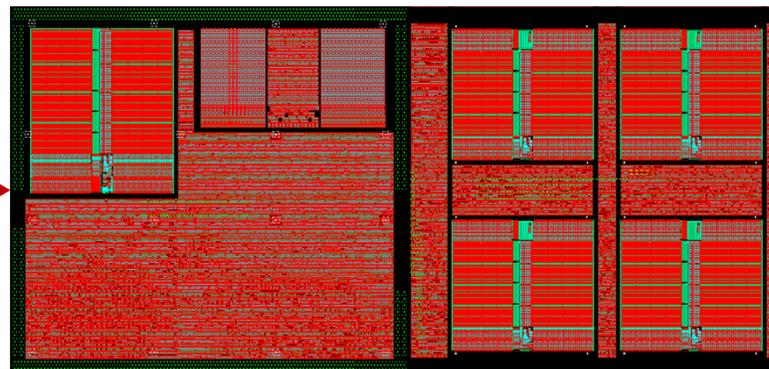
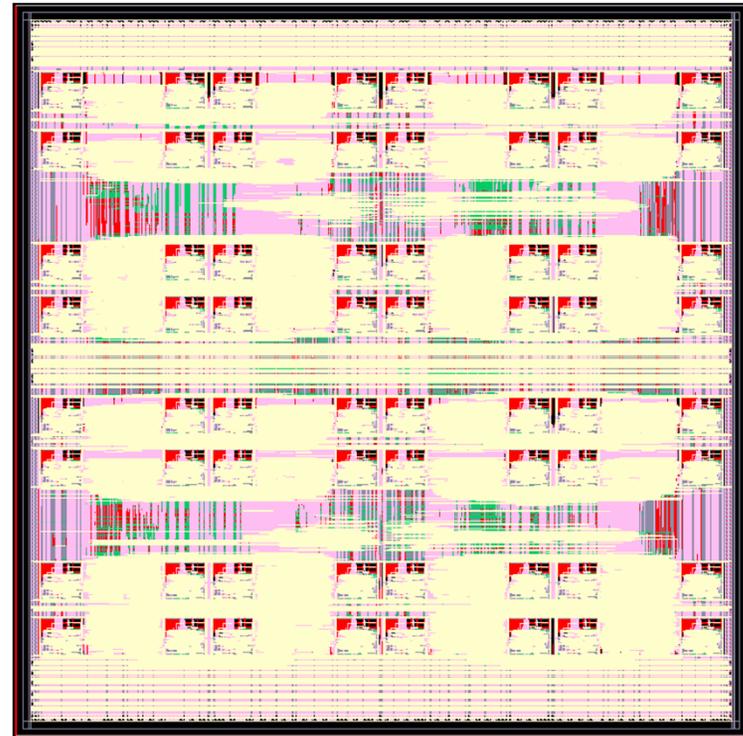
# V2 Layouts

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Top logic die



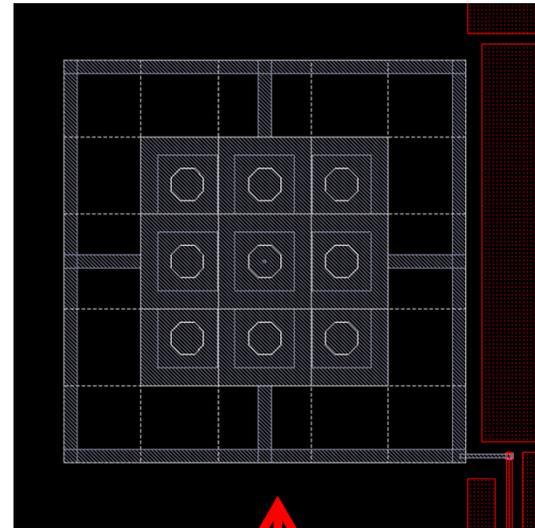
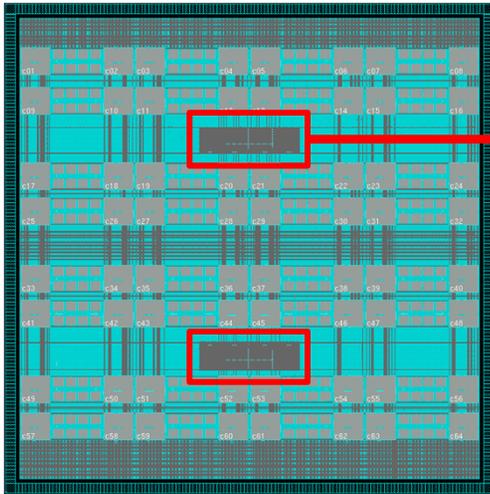
Bot logic die



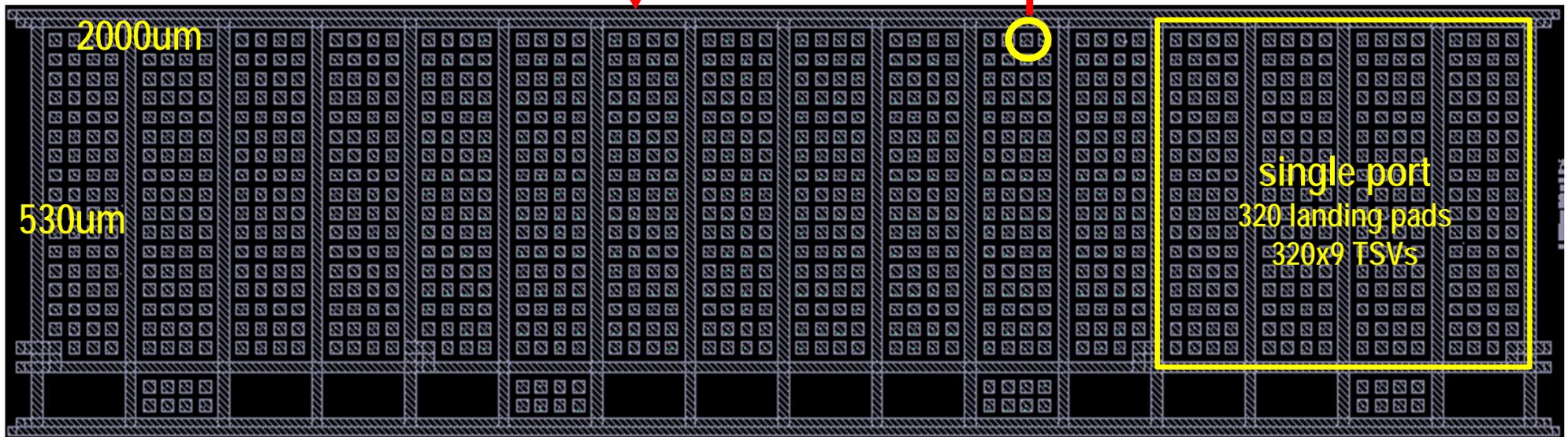
Single core and its scratchpad SRAM (4KB)

# Wide-I/O DRAM Interface

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Each M1 landing pad has 9 redundant TSVs



# Conclusions

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- 3D-MAPS V1
  - 64 general-purpose cores + stacked SRAM
  - Ran 8 parallel applications successfully
  - Achieved 64GB/s memory bandwidth @ 4W power
  - Developed CAD tools and methodologies
  - TSV used for I/O
- 3D-MAPS V2 (ongoing work)
  - 128 cores + stacked SRAM & DRAM cube
  - TSV used for I/O and DRAM access